



## TLVx316

## 10-MHz, Rail-to-Rail Input/Output, Low-Voltage, 1.8-V CMOS Operational Amplifiers

## 1 Features

- Unity-Gain Bandwidth: 10 MHz
- Low  $I_Q$ : 400  $\mu\text{A}/\text{ch}$ 
  - Excellent Power-to-Bandwidth Ratio
  - Stable  $I_Q$  Over Temperature and Supply Range
- Wide Supply Range: 1.8 V to 5.5 V
- Low Noise: 12  $\text{nV}/\sqrt{\text{Hz}}$  at 1 kHz
- Low Input Bias Current:  $\pm 10$  pA
- Offset Voltage:  $\pm 0.75$  mV
- Unity-Gain Stable
- Internal RFI/EMI Filter
- Extended Temperature Range:  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$

## 2 Applications

- Battery-Powered Instruments:
  - Consumer, Industrial, Medical
  - Notebooks, Portable Media Players
- Sensor Signal Conditioning
- Barcode Scanners
- Active Filters
- Audio

## 3 Description

The TLV316 (single), TLV2316 (dual), and TLV4316 (quad) devices comprise a family of general-purpose, low-power operational amplifiers. Features such as rail-to-rail input and output swings, low quiescent current (400  $\mu\text{A}/\text{ch}$  typical) combined with a wide bandwidth of 10 MHz, and very-low noise (12  $\text{nV}/\sqrt{\text{Hz}}$  at 1 kHz) make this family attractive for a variety of applications that require a good balance between cost and performance. The low input bias current supports operational amplifiers that are used in applications with megaohm source impedances.

The robust design of the TLV316 devices provides ease-of-use to the circuit designer—a unity-gain stable, integrated RFI/EMI rejection filter, no phase reversal in overdrive condition, and high electrostatic discharge (ESD) protection (4-kV HBM).

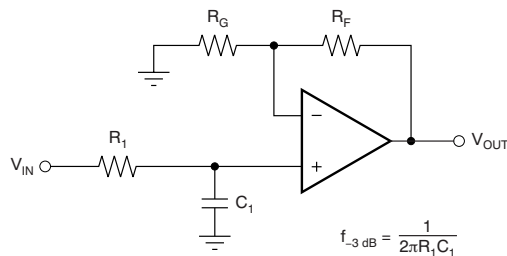
These devices are optimized for low-voltage operation as low as 1.8 V ( $\pm 0.9$  V) and up to 5.5 V ( $\pm 2.75$  V). This latest addition of low-voltage CMOS operational amplifiers to the portfolio, in conjunction with the [TLVx313](#) and [TLVx314](#), offer a family of bandwidth, noise, and power options to meet the needs of a wide variety of applications.

Device Information<sup>(1)</sup>

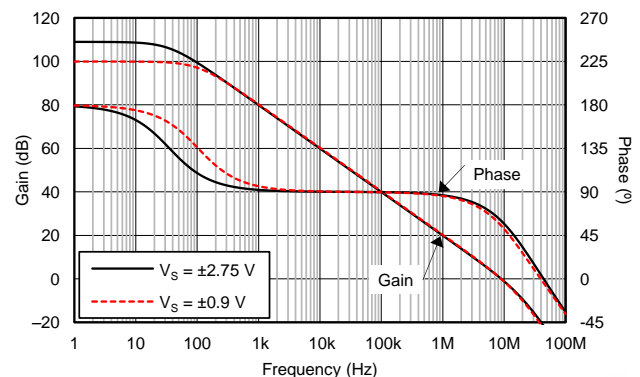
PART NUMBER	PACKAGE	BODY SIZE (NOM)
TLV316	SC70 (5)	1.25 mm × 2.00 mm
	SOT-23 (5)	1.60 mm × 2.90 mm
TLV2316	VSSOP (8)	3.00 mm × 3.00 mm
	SOIC (8)	3.91 mm × 4.90 mm
TLV4316	TSSOP (14)	4.40 mm × 5.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

## Single-Pole, Low-Pass Filter



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_I C_1}\right)$$

Low Supply Current (400  $\mu\text{A}/\text{Ch}$ ) for 10-MHz Bandwidth

## Table of Contents

<b>1 Features</b> .....	<b>1</b>	8.3 Feature Description .....	<b>14</b>
<b>2 Applications</b> .....	<b>1</b>	8.4 Device Functional Modes .....	<b>15</b>
<b>3 Description</b> .....	<b>1</b>	<b>9 Application and Implementation</b> .....	<b>16</b>
<b>4 Revision History</b> .....	<b>2</b>	9.1 Application Information .....	<b>16</b>
<b>5 Device Comparison Table</b> .....	<b>3</b>	9.2 System Examples .....	<b>16</b>
<b>6 Pin Configuration and Functions</b> .....	<b>3</b>	<b>10 Power Supply Recommendations</b> .....	<b>17</b>
<b>7 Specifications</b> .....	<b>6</b>	10.1 Input and ESD Protection .....	<b>17</b>
7.1 Absolute Maximum Ratings .....	<b>6</b>	<b>11 Layout</b> .....	<b>18</b>
7.2 ESD Ratings .....	<b>6</b>	11.1 Layout Guidelines .....	<b>18</b>
7.3 Recommended Operating Conditions .....	<b>6</b>	11.2 Layout Example .....	<b>18</b>
7.4 Thermal Information: TLV316 .....	<b>7</b>	<b>12 Device and Documentation Support</b> .....	<b>19</b>
7.5 Thermal Information: TLV2316 .....	<b>7</b>	12.1 Documentation Support .....	<b>19</b>
7.6 Thermal Information: TLV4316 .....	<b>7</b>	12.2 Related Links .....	<b>19</b>
7.7 Electrical Characteristics .....	<b>8</b>	12.3 Community Resources .....	<b>19</b>
7.8 Typical Characteristics .....	<b>9</b>	12.4 Trademarks .....	<b>19</b>
7.9 Typical Characteristics .....	<b>10</b>	12.5 Electrostatic Discharge Caution .....	<b>20</b>
<b>8 Detailed Description</b> .....	<b>13</b>	12.6 Glossary .....	<b>20</b>
8.1 Overview .....	<b>13</b>	<b>13 Mechanical, Packaging, and Orderable Information</b> .....	<b>20</b>
8.2 Functional Block Diagram .....	<b>13</b>		

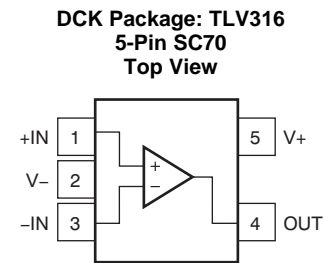
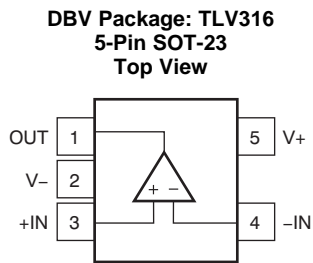
## 4 Revision History

DATE	REVISION	NOTES
February 2016	*	Initial release.

## 5 Device Comparison Table

DEVICE	NO. OF CHANNELS	PACKAGE-LEADS				
		DBV	DCK	D	DGK	PW
TLV316	1	5	5	—	—	—
TLV2316	2	—	—	8	8	—
TLV4316	4	—	—	—	—	14

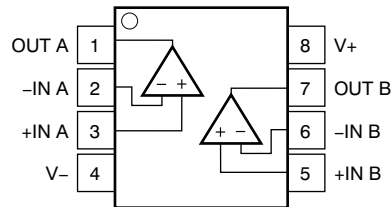
## 6 Pin Configuration and Functions



**Pin Functions: TLV316**

PIN			I/O	DESCRIPTION
NAME	DBV (SOT-23)	DCK (SC70)		
–IN	4	3	I	Inverting input
+IN	3	1	I	Noninverting input
OUT	1	4	O	Output
V–	2	2	—	Negative (lowest) supply or ground (for single-supply operation)
V+	5	5	—	Positive (highest) supply

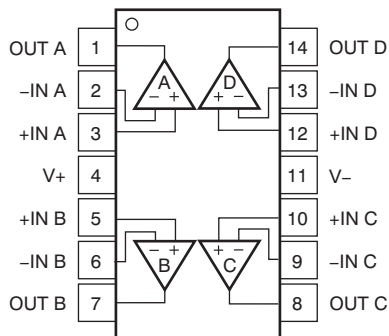
**D, DGK Packages: TLV2316**  
**8-Pin SOIC, VSSOP**  
**Top View**



**Pin Functions: TLV2316**

PIN		I/O	DESCRIPTION
NAME	D (SOIC), DGK (VSSOP)		
-IN A	2	I	Inverting input, channel A
+IN A	3	I	Noninverting input, channel A
-IN B	6	I	Inverting input, channel B
+IN B	5	I	Noninverting input, channel B
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
V-	4	—	Negative (lowest) supply or ground (for single-supply operation)
V+	8	—	Positive (highest) supply

**PW Package: TLV4316  
14-Pin TSSOP  
Top View**



**Pin Functions: TLV4316**

PIN		I/O	DESCRIPTION
NAME	NO.		
-IN A	2	I	Inverting input, channel A
+IN A	3	I	Noninverting input, channel A
-IN B	6	I	Inverting input, channel B
+IN B	5	I	Noninverting input, channel B
-IN C	9	I	Inverting input, channel C
+IN C	10	I	Noninverting input, channel C
-IN D	13	I	Inverting input, channel D
+IN D	12	I	Noninverting input, channel D
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
OUT C	8	O	Output, channel C
OUT D	14	O	Output, channel D
V-	11	—	Negative (lowest) supply or ground (for single-supply operation)
V+	4	—	Positive (highest) supply

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
Supply voltage			7		V
Signal input pins	Voltage <sup>(2)</sup>	Common-mode	(V–) – 0.5	(V+) + 0.5	V
		Differential	(V+) – (V–) + 0.2		
		Current <sup>(2)</sup>	–10	10	mA
Output short-circuit <sup>(3)</sup>			Continuous		mA
Temperature	Specified, T <sub>A</sub>		–40	125	°C
	Junction, T <sub>J</sub>		150		
	Storage, T <sub>stg</sub>		–65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Current limit input signals that can swing more than 0.5 V beyond the supply rails to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.

### 7.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted)

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±4000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>S</sub>	Supply voltage	1.8		5.5	V
	Specified temperature range	–40		125	°C

## 7.4 Thermal Information: TLV316

THERMAL METRIC <sup>(1)</sup>		TLV316		UNIT
		DBV (SOT-23)	DCK (SC70)	
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	221.7	263.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	144.7	75.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	49.7	51.0	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	26.1	1.0	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	49.0	50.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 7.5 Thermal Information: TLV2316

THERMAL METRIC <sup>(1)</sup>		TLV2316		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	127.2	186.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	71.6	78.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	68.2	107.9	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	22.0	15.5	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	67.6	106.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 7.6 Thermal Information: TLV4316

THERMAL METRIC <sup>(1)</sup>		TLV4316	UNIT
		PW (TSSOP)	
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	117.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	46.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	58.9	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	4.9	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	58.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 7.7 Electrical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted);  $V_S$  (total supply voltage) =  $(V+) - (V-) = 1.8\text{ V to } 5.5\text{ V}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V <sub>OS</sub>	Input offset voltage	V <sub>S</sub> = 5 V		±0.75	±3	mV
		V <sub>S</sub> = 5 V, T <sub>A</sub> = −40°C to +125°C			±4.5	
dV <sub>OS</sub> /dT	Drift	V <sub>S</sub> = 5 V, T <sub>A</sub> = −40°C to +125°C		±2		μV/°C
PSRR	Power-supply rejection ratio	V <sub>S</sub> = 1.8 V – 5.5 V, V <sub>CM</sub> = (V−)		±30	±175	μV/V
	Channel separation, dc	At dc		100		dB
INPUT VOLTAGE RANGE						
V <sub>CM</sub>	Common-mode voltage range	V <sub>S</sub> = 5.5 V	(V−) − 0.2		(V+) + 0.2	V
CMRR	Common-mode rejection ratio	V <sub>S</sub> = 5.5 V, (V−) − 0.2 V < V <sub>CM</sub> < (V+) − 1.4 V, T <sub>A</sub> = −40°C to +125°C	72	90		dB
		V <sub>S</sub> = 5.5 V, V <sub>CM</sub> = −0.2 V to 5.7 V, T <sub>A</sub> = −40°C to +125°C		75		
INPUT BIAS CURRENT						
I <sub>B</sub>	Input bias current			±10		pA
I <sub>OS</sub>	Input offset current			±10		pA
NOISE						
E <sub>n</sub>	Input voltage noise (peak-to-peak)	V <sub>S</sub> = 5 V, f = 0.1 Hz to 10 Hz		5		μV <sub>PP</sub>
e <sub>n</sub>	Input voltage noise density	V <sub>S</sub> = 5 V, f = 1 kHz		12		nV/√Hz
i <sub>n</sub>	Input current noise density	f = 1 kHz		1.3		fA/√Hz
INPUT IMPEDANCE						
Z <sub>ID</sub>	Differential			2    2		10 <sup>16</sup> Ω    pF
Z <sub>IC</sub>	Common-mode			2    4		10 <sup>11</sup> Ω    pF
OPEN-LOOP GAIN						
A <sub>OL</sub>	Open-loop voltage gain	V <sub>S</sub> = 5.5 V, (V−) + 0.05 V < V <sub>O</sub> < (V+) − 0.05 V, R <sub>L</sub> = 10 kΩ	100	104		dB
		V <sub>S</sub> = 5.5 V, (V−) + 0.15 V < V <sub>O</sub> < (V+) − 0.15 V, R <sub>L</sub> = 2 kΩ		104		
FREQUENCY RESPONSE						
GBP	Gain bandwidth product	V <sub>S</sub> = 5 V, G = +1		10		MHz
φ <sub>m</sub>	Phase margin	V <sub>S</sub> = 5 V, G = +1		60		Degrees
SR	Slew rate	V <sub>S</sub> = 5 V, G = +1		6		V/μs
t <sub>S</sub>	Settling time	To 0.1%, V <sub>S</sub> = 5 V, 2-V step , G = +1, C <sub>L</sub> = 100 pF		1		μs
t <sub>OR</sub>	Overload recovery time	V <sub>S</sub> = 5 V, V <sub>IN</sub> × gain = V <sub>S</sub>		0.8		μs
THD + N	Total harmonic distortion + noise <sup>(1)</sup>	V <sub>S</sub> = 5 V, V <sub>O</sub> = 0.5 V <sub>RMS</sub> , G = +1, f = 1 kHz		0.008%		
OUTPUT						
V <sub>O</sub>	Voltage output swing from supply rails	V <sub>S</sub> = 1.8 V to 5.5 V, R <sub>L</sub> = 10 kΩ,			35	mV
		V <sub>S</sub> = 1.8 to 5.5 V, R <sub>L</sub> = 2 kΩ,			125	
I <sub>SC</sub>	Short-circuit current	V <sub>S</sub> = 5 V		±50		mA
Z <sub>O</sub>	Open-loop output impedance	V <sub>S</sub> = 5 V, f = 10 MHz		250		Ω
POWER SUPPLY						
V <sub>S</sub>	Specified voltage range		1.8		5.5	V
I <sub>Q</sub>	Quiescent current per amplifier	V <sub>S</sub> = 5 V, I <sub>O</sub> = 0 mA, T <sub>A</sub> = −40°C to 125°C		400	575	μA
TEMPERATURE						
T <sub>A</sub>	Specified		−40		125	°C
T <sub>stg</sub>	Storage		−65		150	°C

(1) Third-order filter; bandwidth = 80 kHz at -3 dB.

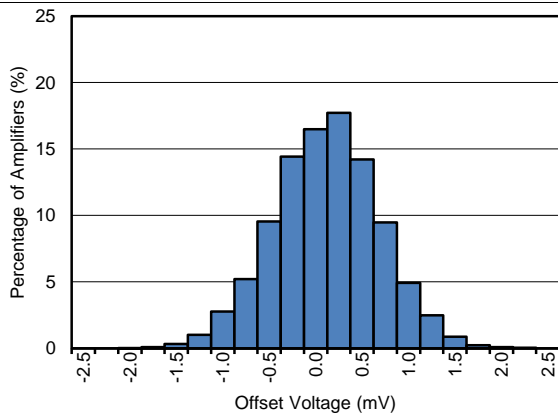
## 7.8 Typical Characteristics

**Table 1. Table of Graphs**

TITLE	FIGURE
Offset Voltage Production Distribution	<a href="#">Figure 1</a>
Offset Voltage vs Common-Mode Voltage	<a href="#">Figure 2</a>
Open-Loop Gain and Phase vs Frequency	<a href="#">Figure 3</a>
Input Bias and Offset Current vs Temperature	<a href="#">Figure 4</a>
Input Voltage Noise Spectral Density vs Frequency	<a href="#">Figure 5</a>
Quiescent Current vs Supply Voltage	<a href="#">Figure 6</a>
Small-Signal Overshoot vs Load Capacitance	<a href="#">Figure 7</a>
No Phase Reversal	<a href="#">Figure 8</a>
Small-Signal Step Response	<a href="#">Figure 9</a>
Large-Signal Step Response	<a href="#">Figure 10</a>
Short-Circuit Current vs Temperature	<a href="#">Figure 11</a>
Electromagnetic Interference Rejection Ratio Referred to Noninverting Input vs Frequency	<a href="#">Figure 12</a>
Channel Separation vs Frequency	<a href="#">Figure 13</a>

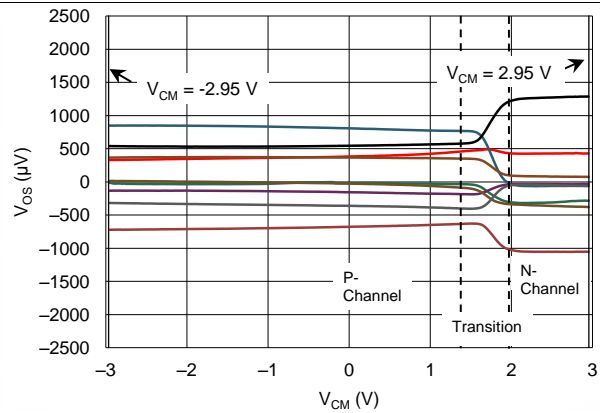
## 7.9 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5.5\text{ V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)



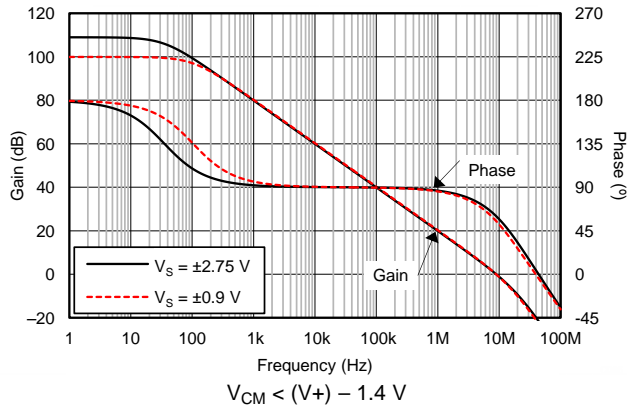
Distribution taken from 12551 amplifiers

**Figure 1. Offset Voltage Production Distribution**

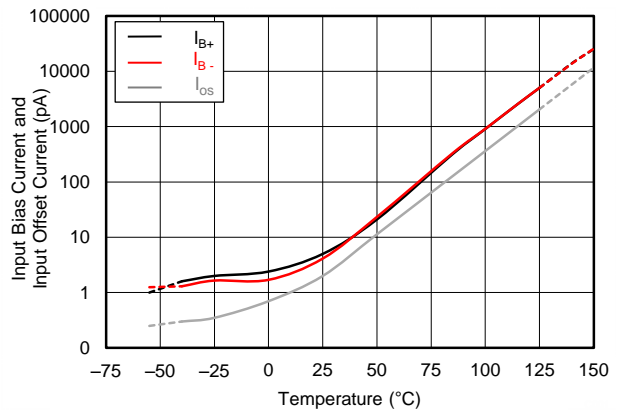


$V_+ = 2.75\text{ V}$ ,  $V_- = -2.75\text{ V}$ , 9 typical units shown

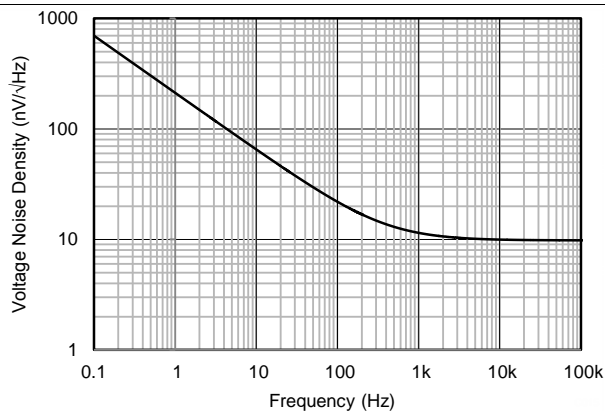
**Figure 2. Offset Voltage vs Common-Mode Voltage**



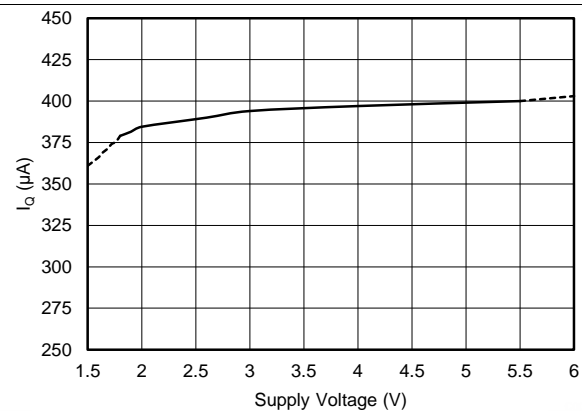
**Figure 3. Open-Loop Gain and Phase vs Frequency**



**Figure 4. Input Bias and Offset Current vs Temperature**



**Figure 5. Input Voltage Noise Spectral Density vs Frequency**



**Figure 6. Quiescent Current vs Supply Voltage**

## Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5.5\text{ V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)

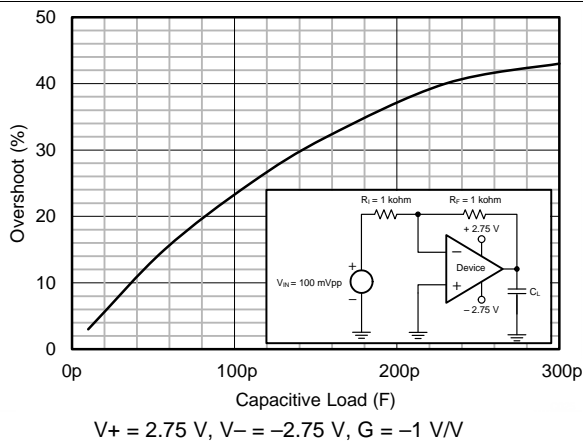


Figure 7. Small-Signal Overshoot vs Load Capacitance

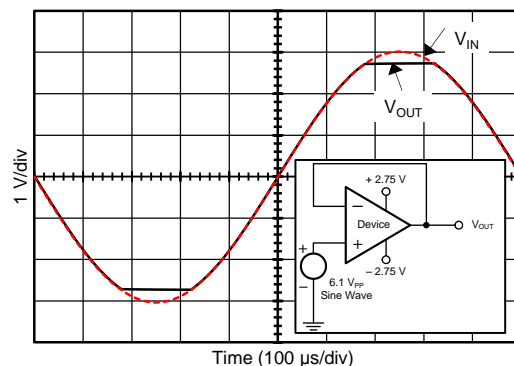


Figure 8. No Phase Reversal

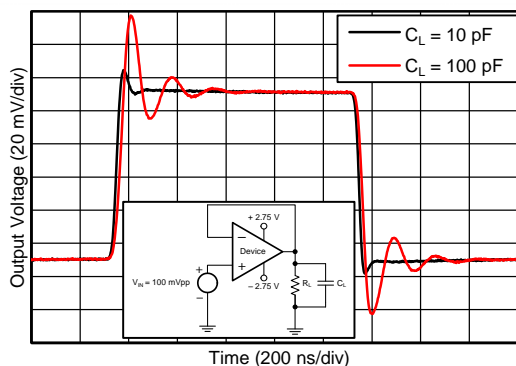


Figure 9. Small-Signal Step Response

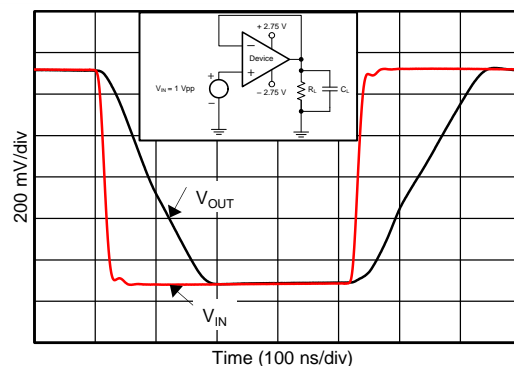


Figure 10. Large-Signal Step Response

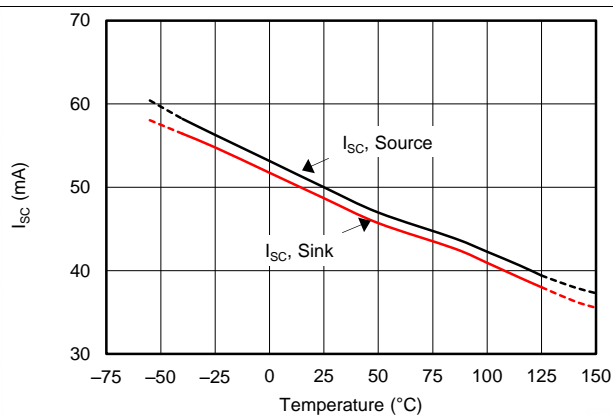


Figure 11. Short-Circuit Current vs Temperature

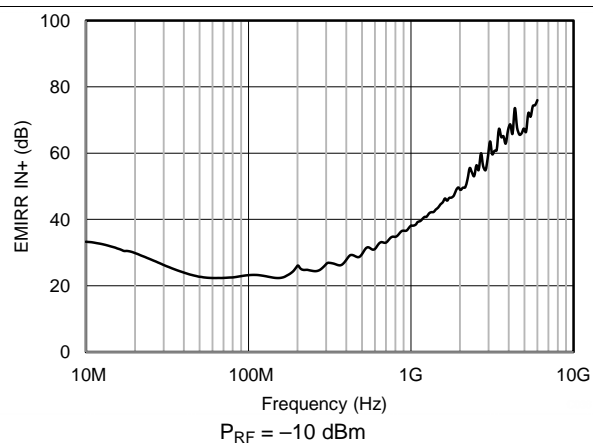
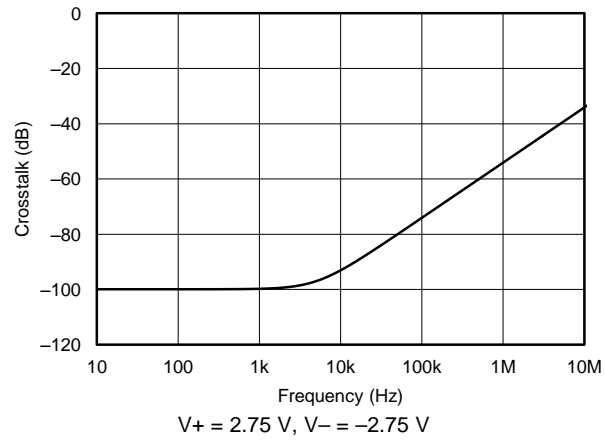


Figure 12. Electromagnetic Interference Rejection Ratio Referred to Noninverting Input vs Frequency

## Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5.5\text{ V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)



**Figure 13. Channel Separation vs Frequency**

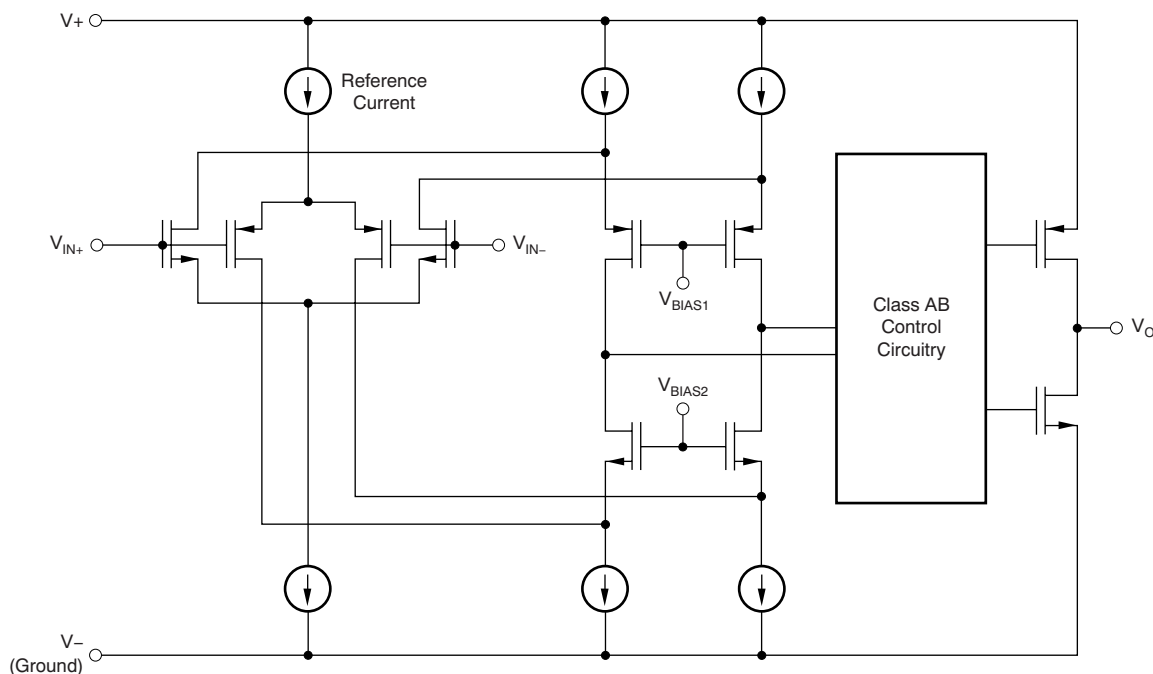
## 8 Detailed Description

### 8.1 Overview

The TLV316 is a family of low-power, rail-to-rail input and output operational amplifiers. These devices operate from 1.8 V to 5.5 V, are unity-gain stable, and are suitable for a wide range of general-purpose applications. The class AB output stage is capable of driving  $\leq 10\text{-k}\Omega$  loads connected to any point between  $V_+$  and ground. The input common-mode voltage range includes both rails and allows the TLV316 series to be used in virtually any single-supply application. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications, and makes them ideal for driving sampling analog-to-digital converters (ADCs).

The TLV316 features 10-MHz bandwidth and 6-V/ $\mu\text{s}$  slew rate with only 400- $\mu\text{A}$  supply current per channel, providing good ac performance at very-low power consumption. DC applications are also well served with a very-low input noise voltage of 12 nV/ $\sqrt{\text{Hz}}$  at 1 kHz, low input bias current (5 pA), and an input offset voltage of 0.5 mV (typical).

### 8.2 Functional Block Diagram



## 8.3 Feature Description

### 8.3.1 Operating Voltage

The TLV316 series operational amplifiers are fully specified and ensured for operation from 1.8 V to 5.5 V. In addition, many specifications apply from  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ . Parameters that vary significantly with operating voltages or temperature are illustrated in the [Typical Characteristics](#) section.

### 8.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLV316 series extends 200 mV beyond the supply rails for supply voltages greater than 2.5 V. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair; see the [Functional Block Diagram](#) section. The N-channel pair is active for input voltages close to the positive rail, typically  $(V+) - 1.4\text{ V}$  to 200 mV above the positive supply, whereas the P-channel pair is active for inputs from 200 mV below the negative supply to approximately  $(V+) - 1.4\text{ V}$ . There is a small transition region, typically  $(V+) - 1.2\text{ V}$  to  $(V+) - 1\text{ V}$ , in which both pairs are on. This 200-mV transition region can vary up to 200 mV with process variation. Thus, the transition region (both stages on) can range from  $(V+) - 1.4\text{ V}$  to  $(V+) - 1.2\text{ V}$  on the low end, up to  $(V+) - 1\text{ V}$  to  $(V+) - 0.8\text{ V}$  on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD can be degraded compared to device operation outside this region.

### 8.3.3 Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the TLV316 delivers a robust output drive capability. A class AB output stage with common-source transistors is used to achieve full rail-to-rail output swing capability. For resistive loads of 10 k $\Omega$ , the output swings typically to within 30 mV of either supply rail regardless of the power-supply voltage applied. Different load conditions change the ability of the amplifier to swing close to the rails; see typical characteristic graph *Output Voltage Swing vs Output Current* ().

### 8.3.4 Common-Mode Rejection Ratio (CMRR)

CMRR for the TLV316 is specified in two ways so the best match for a given application can be selected. First, the [Electrical Characteristics](#) table provides the CMRR of the device in the common-mode range below the transition region [ $V_{\text{CM}} < (V+) - 1.4\text{ V}$ ]. This specification is the best indicator of device capability when the application requires using one of the differential input pairs. Second, the CMRR over the entire common-mode range is specified at  $V_{\text{CM}} = -0.2\text{ V}$  to  $5.7\text{ V}$  for  $V_{\text{S}} = 5.5\text{ V}$ . This last value includes the variations through the transition region.

### 8.3.5 Capacitive Load and Stability

The TLV316 is designed to be used in applications where driving a capacitive load is required. As with all operational amplifiers, there may be specific instances where the TLV316 can become unstable. The particular operational amplifier circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether or not an amplifier is stable in operation. An operational amplifier in the unity-gain (1 V/V) buffer configuration that drives a capacitive load exhibits a greater tendency to be unstable than an amplifier operated at a higher noise gain. The capacitive load, in conjunction with the operational amplifier output resistance, creates a pole within the feedback loop that degrades the phase margin. The degradation of the phase margin increases when the capacitive loading increases. For a conservative best practice, designing for 25% overshoot (40° phase margin) provides improved stability over process variations. The equivalent series resistance (ESR) of some very-large capacitors ( $C_{\text{L}}$  greater than 1  $\mu\text{F}$ ) is sufficient to alter the phase characteristics in the feedback loop such that the amplifier remains stable. Increasing the amplifier closed-loop gain allows the amplifier to drive increasingly larger capacitance. This increased capability is evident when observing the overshoot response of the amplifier at higher voltage gains. See typical characteristic graph, *Small-Signal Overshoot vs Capacitive Load* ([Figure 7](#),  $G = -1\text{ V/V}$ ).

## Feature Description (continued)

One technique for increasing the capacitive load drive capability of the amplifier operating in a unity-gain configuration is to insert a small resistor (typically  $10\ \Omega$  to  $20\ \Omega$ ) in series with the output, as shown in Figure 14. This resistor significantly reduces the overshoot and ringing associated with large capacitive loads. One possible problem with this technique, however, is that a voltage divider is created with the added series resistor and any resistor connected in parallel with the capacitive load. The voltage divider introduces a gain error at the output that reduces the output swing.

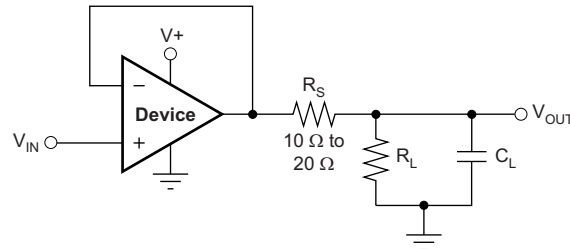


Figure 14. Improving Capacitive Load Drive

### 8.3.6 EMI Susceptibility and Input Filtering

Operational amplifiers vary with regard to the susceptibility of the device to electromagnetic interference (EMI). If conducted EMI enters the operational amplifier, the dc offset measured at the amplifier output can shift from its nominal value when EMI is present. This shift is a result of signal rectification associated with the internal semiconductor junctions. Although all operational amplifier pin functions can be affected by EMI, the signal input pins are likely to be the most susceptible. The TLV316 operational amplifier family incorporates an internal input low-pass filter that reduces the amplifier response to EMI. This filter provides both common-mode and differential-mode filtering. The filter is designed for a cutoff frequency of approximately 80 MHz ( $-3\ \text{dB}$ ), with a roll-off of 20 dB per decade.

The immunity of an operational amplifier can be accurately measured and quantified over a broad frequency spectrum extending from 10 MHz to 6 GHz. The EMI rejection ratio (EMIRR) metric allows operational amplifiers to be directly compared by the EMI immunity. Figure 12 illustrates the results of this testing on the TLV316. Detailed information can also be found in application report, *EMI Rejection Ratio of Operational Amplifiers* (SBOA128), available for download from [www.ti.com](http://www.ti.com).

### 8.3.7 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, either because of the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return back to the linear state. After the charge carriers return back to the linear state, the device begins to slew at the specified slew rate. Thus, the propagation delay in case of an overload condition is the sum of the overload recovery time and the slew time. The overload recovery time for the TLV316 is approximately 300 ns.

## 8.4 Device Functional Modes

The TLVx316 devices have a single functional mode. These devices are powered on as long as the power-supply voltage is between 1.8 V ( $\pm 0.9\ \text{V}$ ) and 5.5 V ( $\pm 2.75\ \text{V}$ ).

## 9 Application and Implementation

### NOTE

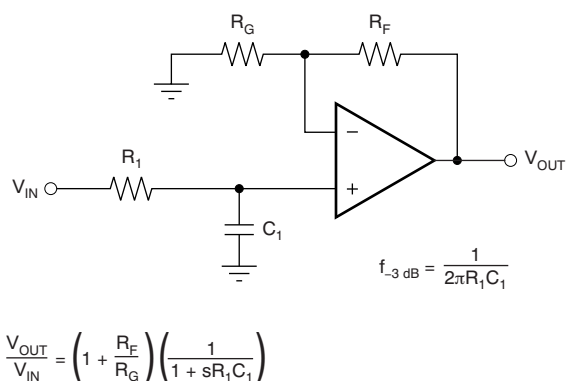
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The TLV316, TLV2316, and TLV4316 are powered on when the supply is connected. The devices can be operated as a single-supply operational amplifier or a dual-supply amplifier, depending on the application.

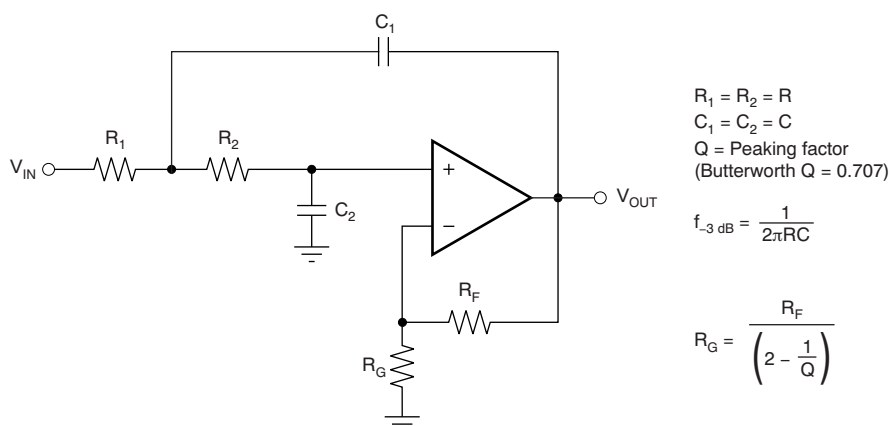
### 9.2 System Examples

When receiving low-level signals, the device often requires limiting the bandwidth of the incoming signals into the system. The simplest way to establish this limited bandwidth is to place an RC filter at the noninverting pin of the amplifier, as shown in [Figure 15](#).



**Figure 15. Single-Pole, Low-Pass Filter**

If even more attenuation is needed, the device requires a multiple-pole filter. The Sallen-Key filter can be used for this task, as shown in [Figure 16](#). For best results, the amplifier must have a bandwidth that is eight to ten times the filter frequency bandwidth. Failure to follow this guideline can result in a phase shift of the amplifier.



**Figure 16. Two-Pole, Low-Pass, Sallen-Key Filter**

## 10 Power Supply Recommendations

The TLV316 is specified for operation from 1.8 V to 5.5 V ( $\pm 0.9$  V to  $\pm 2.75$  V); many specifications apply from  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ . The [Typical Characteristics](#) section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

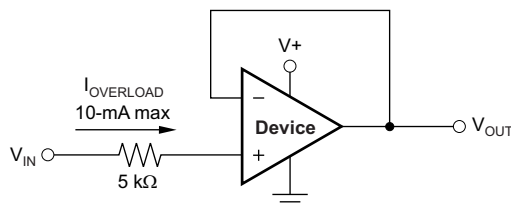
### CAUTION

Supply voltages larger than 7 V can permanently damage the device (see the [Absolute Maximum Ratings](#) table).

Place 0.1- $\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the [Layout Guidelines](#) section.

### 10.1 Input and ESD Protection

The TLV316 family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA as stated in the [Absolute Maximum Ratings](#) table. [Figure 17](#) shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and its value must be kept to a minimum in noise-sensitive applications.



**Figure 17. Input Current Protection**

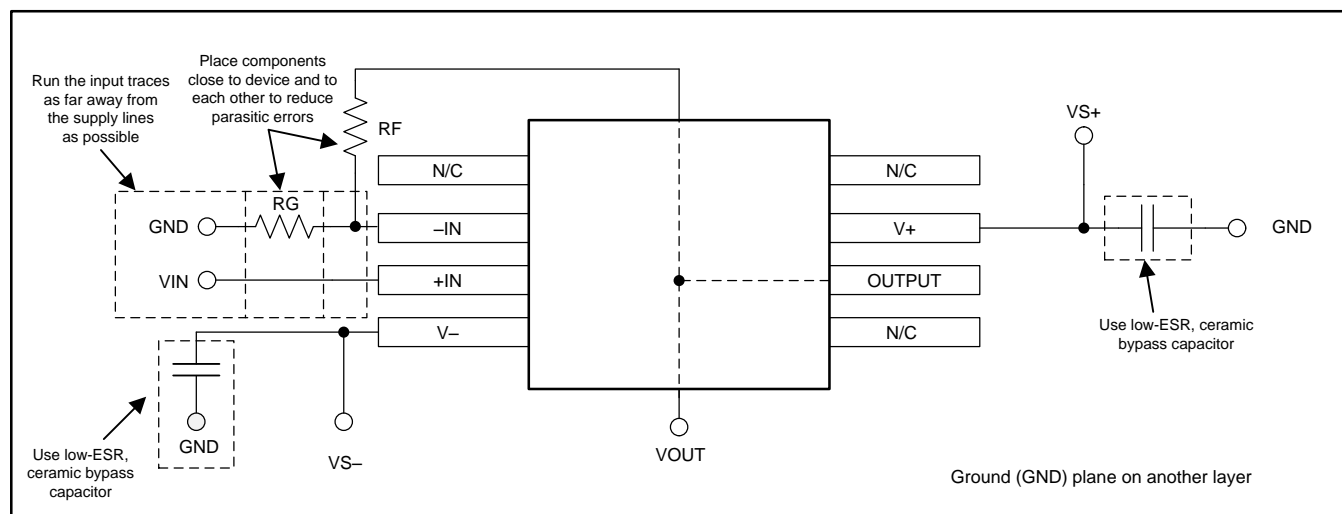
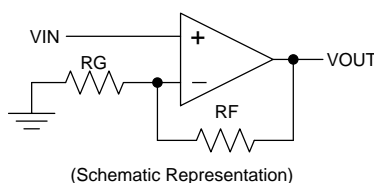
## 11 Layout

### 11.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1- $\mu$ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*, [SLOA089](#).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in [Layout Example](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

### 11.2 Layout Example



**Figure 18. Operational Amplifier Board Layout for a Noninverting Configuration**

## 12 Device and Documentation Support

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

TLVx313 Data Sheet, [SBOS753](#)

TLVx314 Data Sheet, [SBOS754](#)

*EMI Rejection Ratio of Operational Amplifiers*, [SBOA128](#)

*QFN/SON PCB Attachment*, [SLUA271](#)

*Quad Flatpack No-Lead Logic Packages*, [SCBA017](#)

*Circuit Board Layout Techniques*, [SLOA089](#)

*Single-Ended Input to Differential Output Conversion Circuit Reference Design*, [TIPD131](#)

### 12.2 Related Links

[Table 2](#) lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

**Table 2. Related Links**

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TLV316	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>
TLV2316	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>
TLV4316	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>

### 12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](#), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

## 12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV2316IDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	12X6	<a href="#">Samples</a>
TLV2316IDGKT	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	12X6	<a href="#">Samples</a>
TLV2316IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	V2316	<a href="#">Samples</a>
TLV316IDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12C	<a href="#">Samples</a>
TLV316IDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12C	<a href="#">Samples</a>
TLV316IDCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	12D	<a href="#">Samples</a>
TLV316IDCKT	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	12D	<a href="#">Samples</a>
TLV4316IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV4316	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

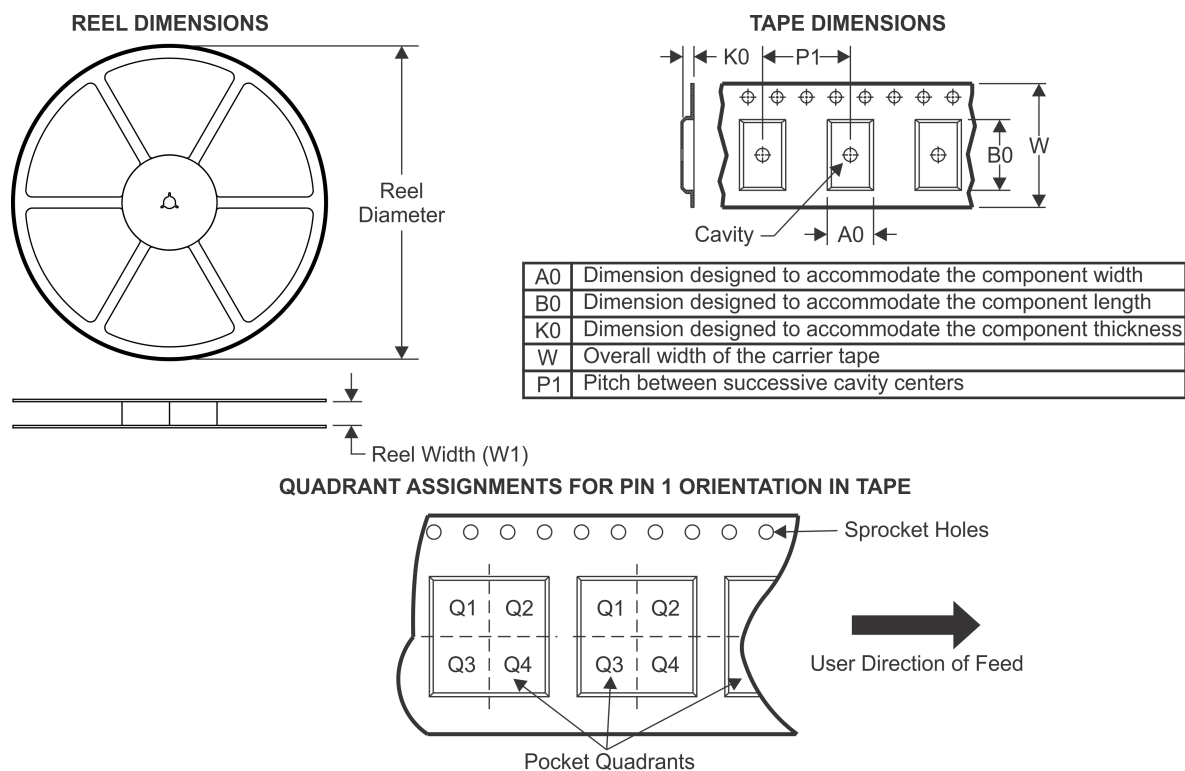
<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

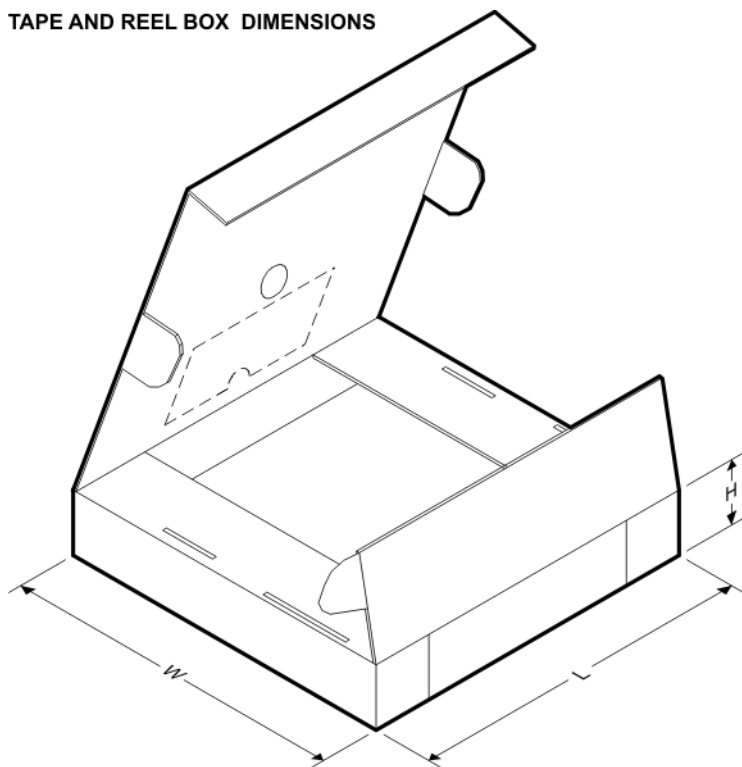
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2316IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2316IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2316IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV316IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV316IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV316IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV316IDCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV4316IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

## TAPE AND REEL BOX DIMENSIONS

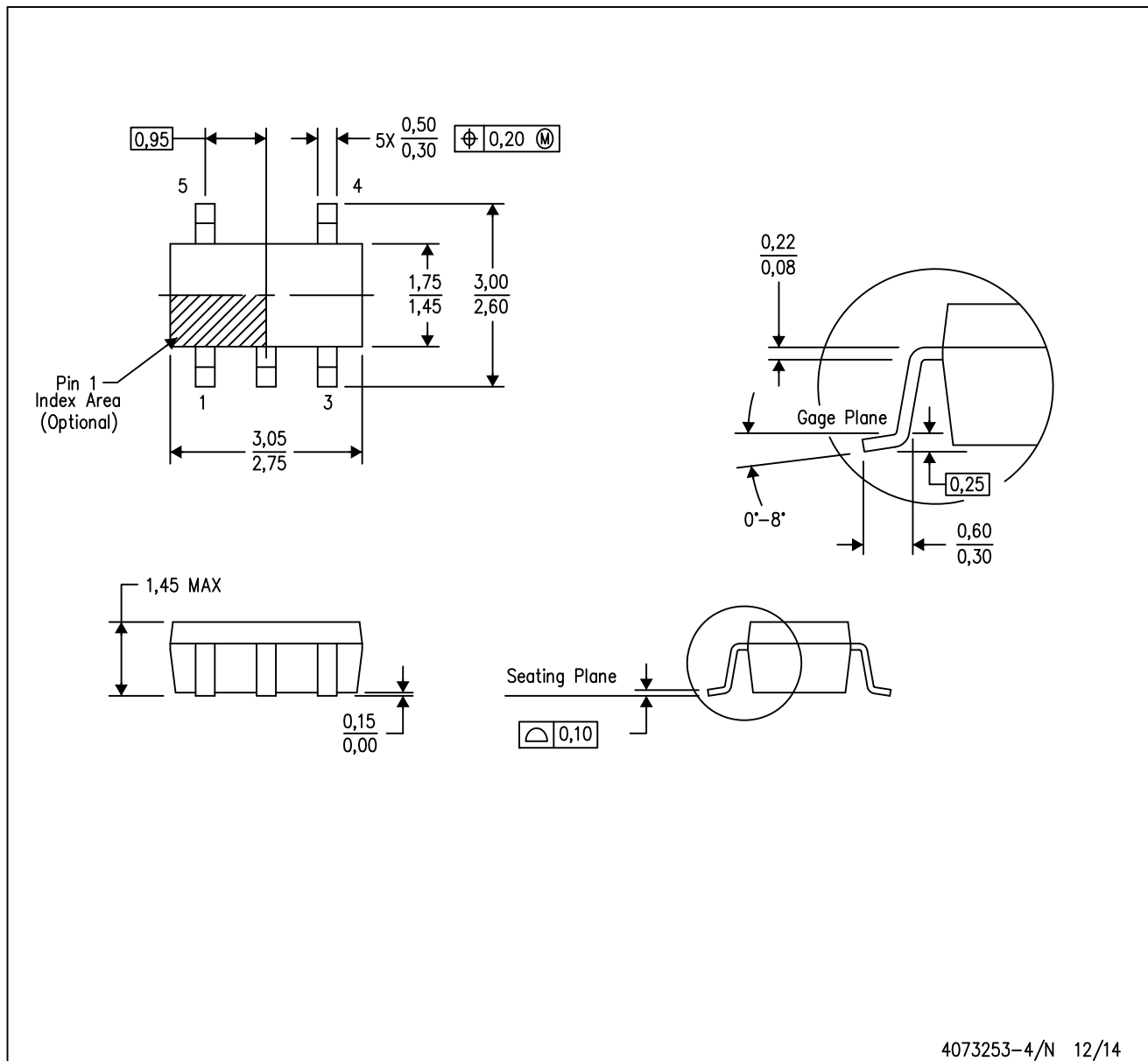


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2316IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
TLV2316IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
TLV2316IDR	SOIC	D	8	2500	367.0	367.0	35.0
TLV316IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV316IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV316IDCKR	SC70	DCK	5	3000	180.0	180.0	18.0
TLV316IDCKT	SC70	DCK	5	250	180.0	180.0	18.0
TLV4316IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0

DBV (R-PDSO-G5)

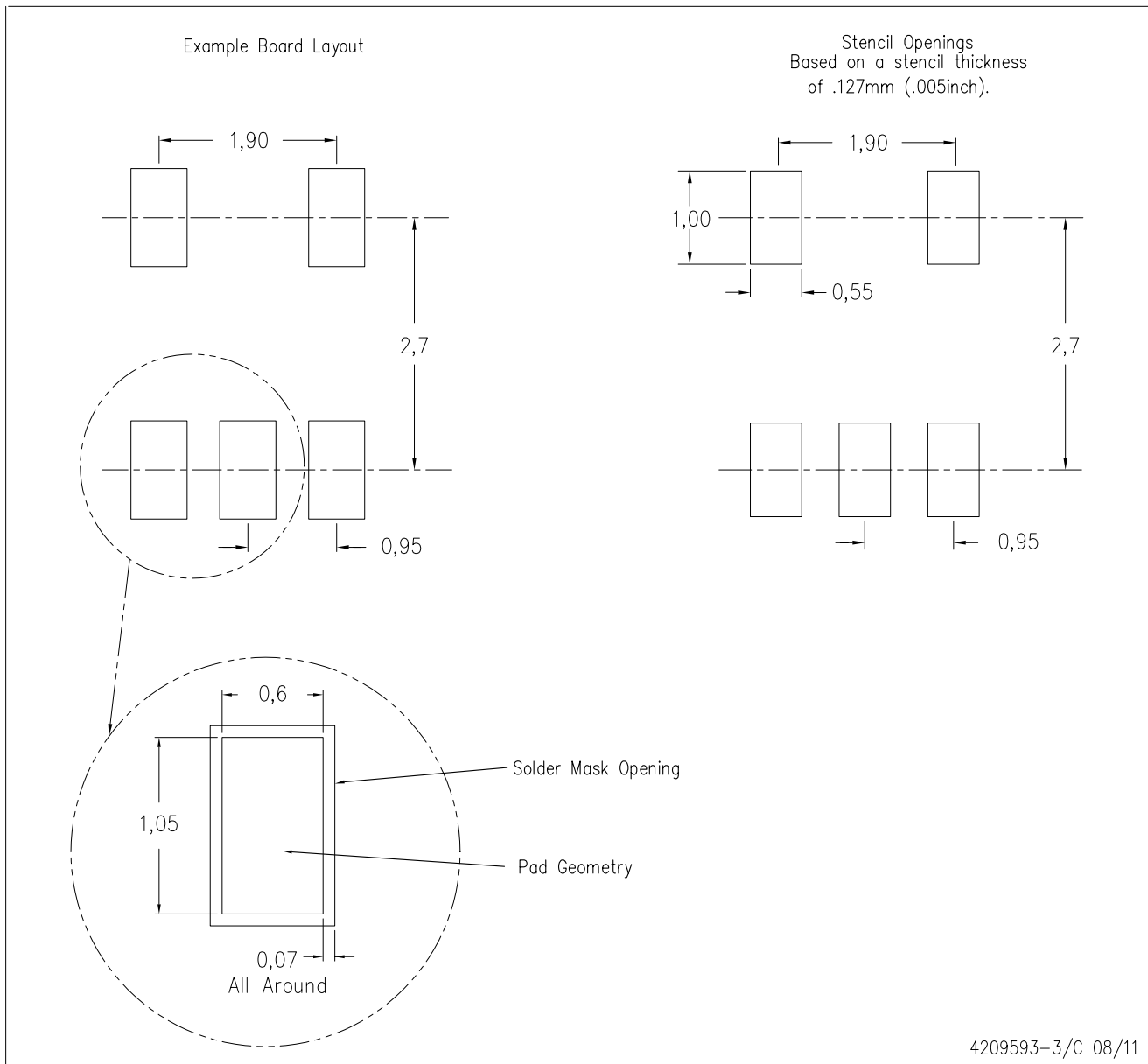
PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - D. Falls within JEDEC MO-178 Variation AA.

DBV (R-PDSO-G5)

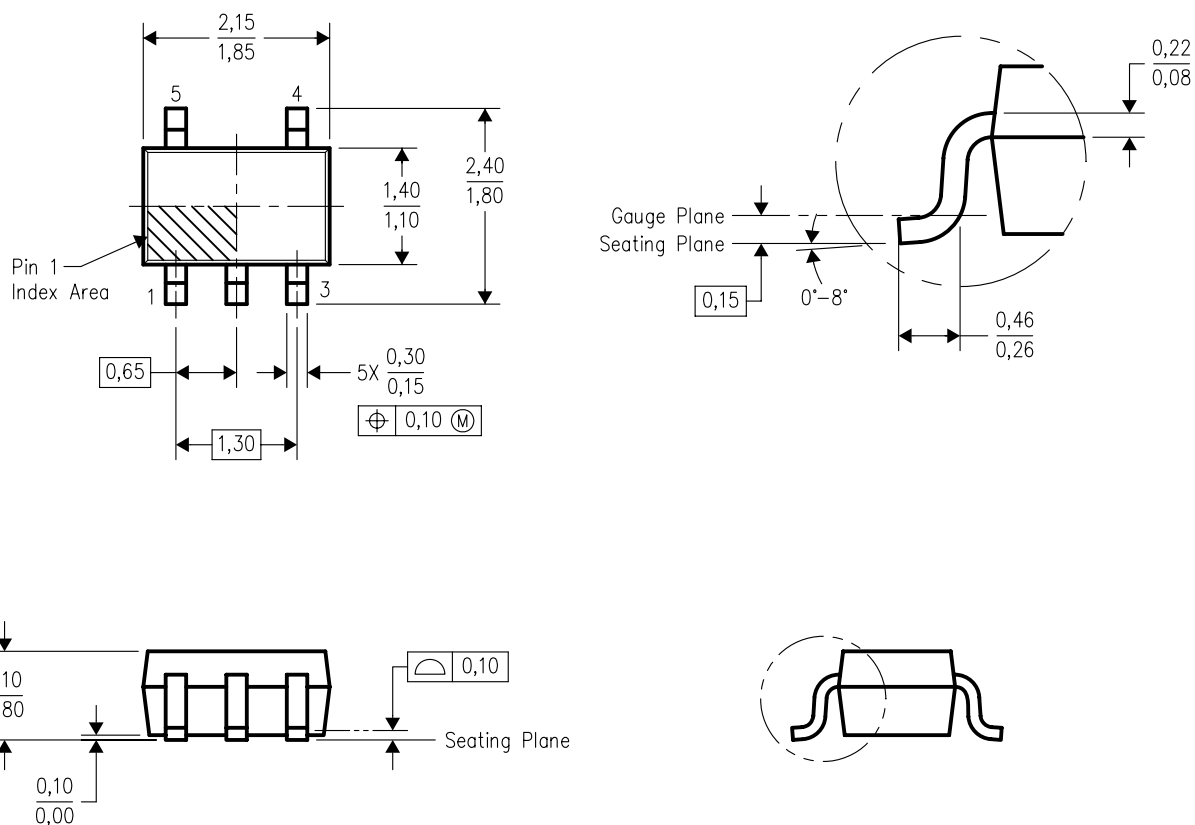
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
  - D. Publication IPC-7351 is recommended for alternate designs.
  - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

## DCK (R-PDSO-G5)

## PLASTIC SMALL-OUTLINE PACKAGE

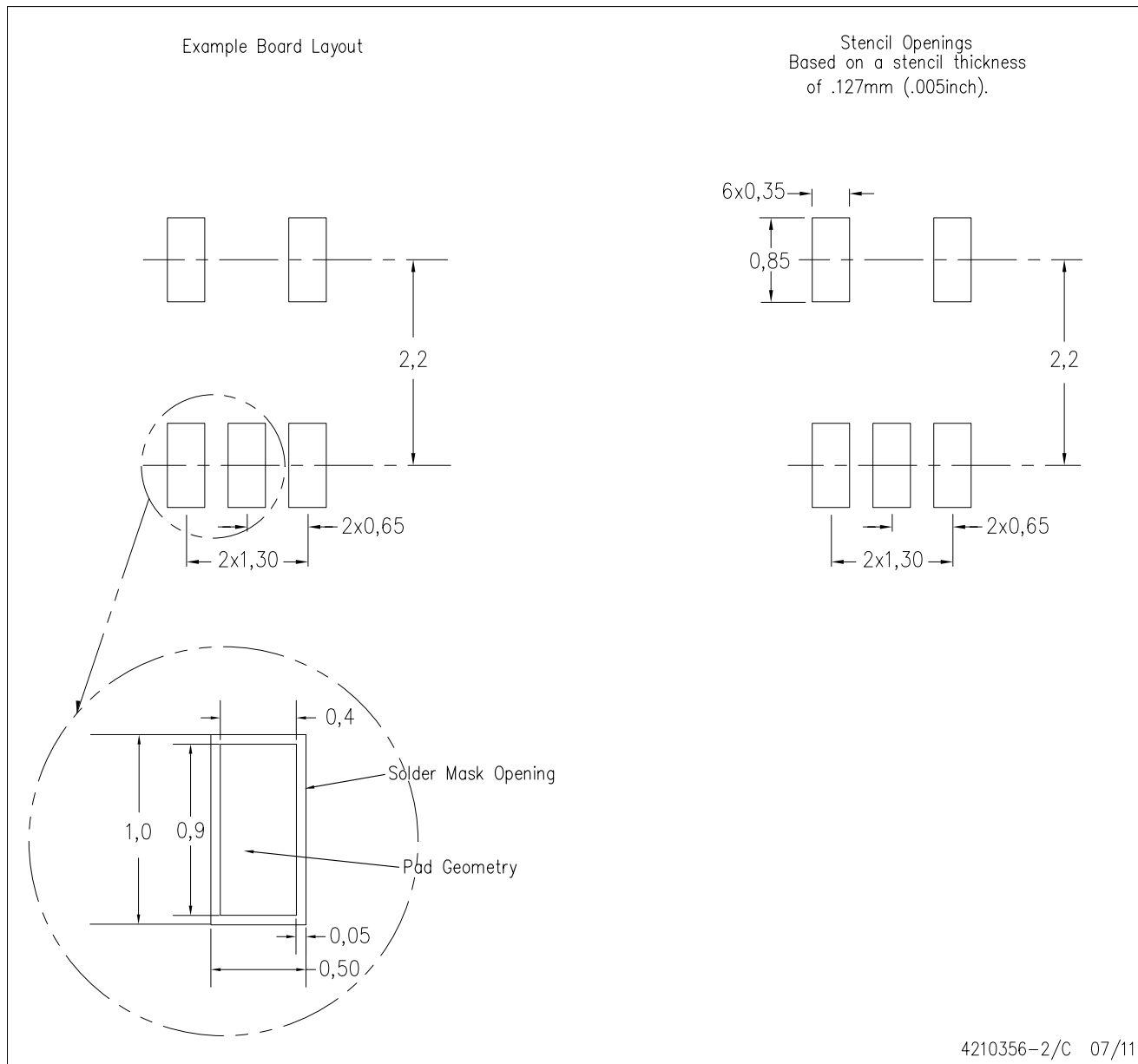


4093553-3/G 01/2007

- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

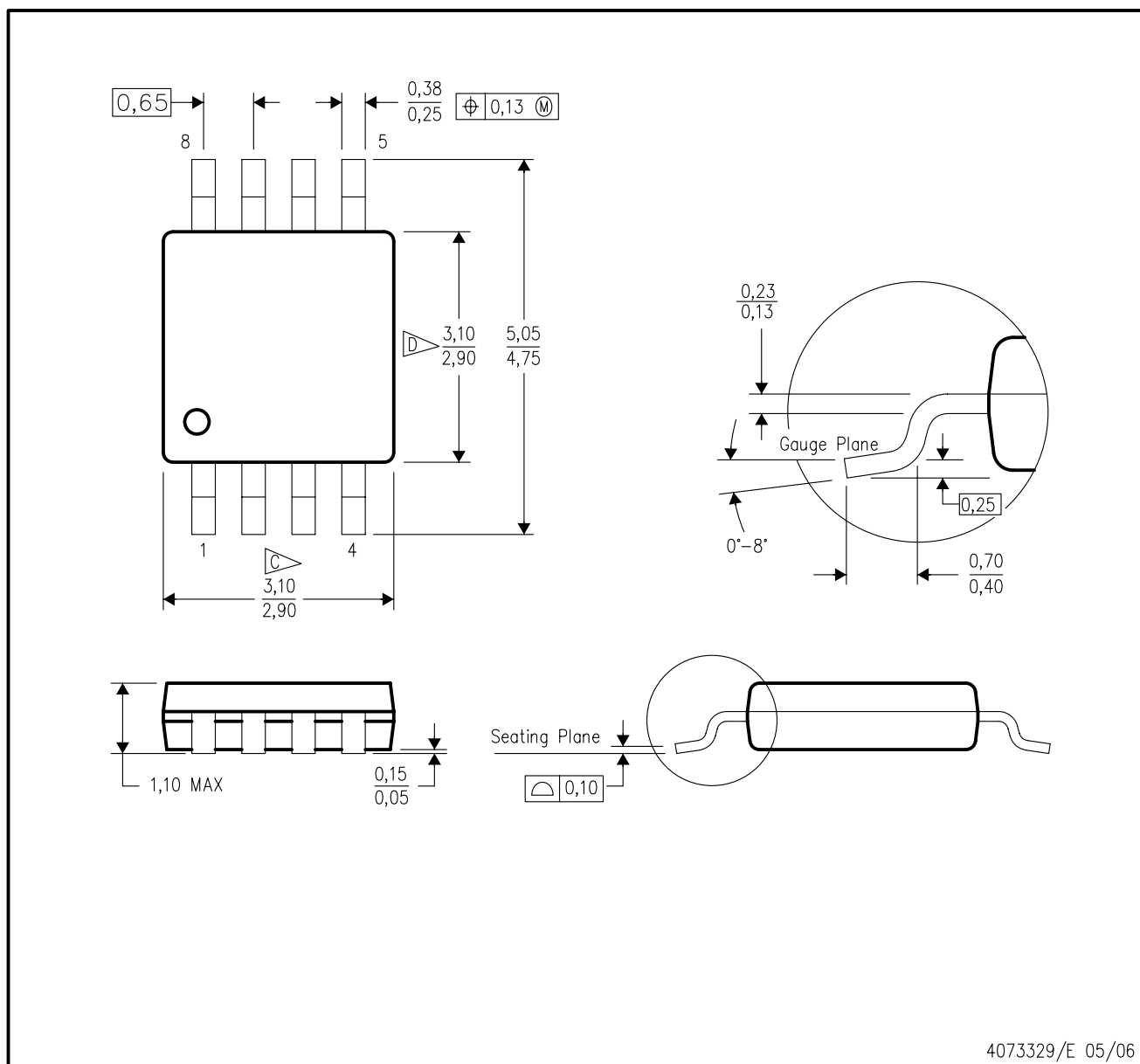
PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
  - Publication IPC-7351 is recommended for alternate designs.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

## DGK (S-PDSO-G8)

## PLASTIC SMALL-OUTLINE PACKAGE

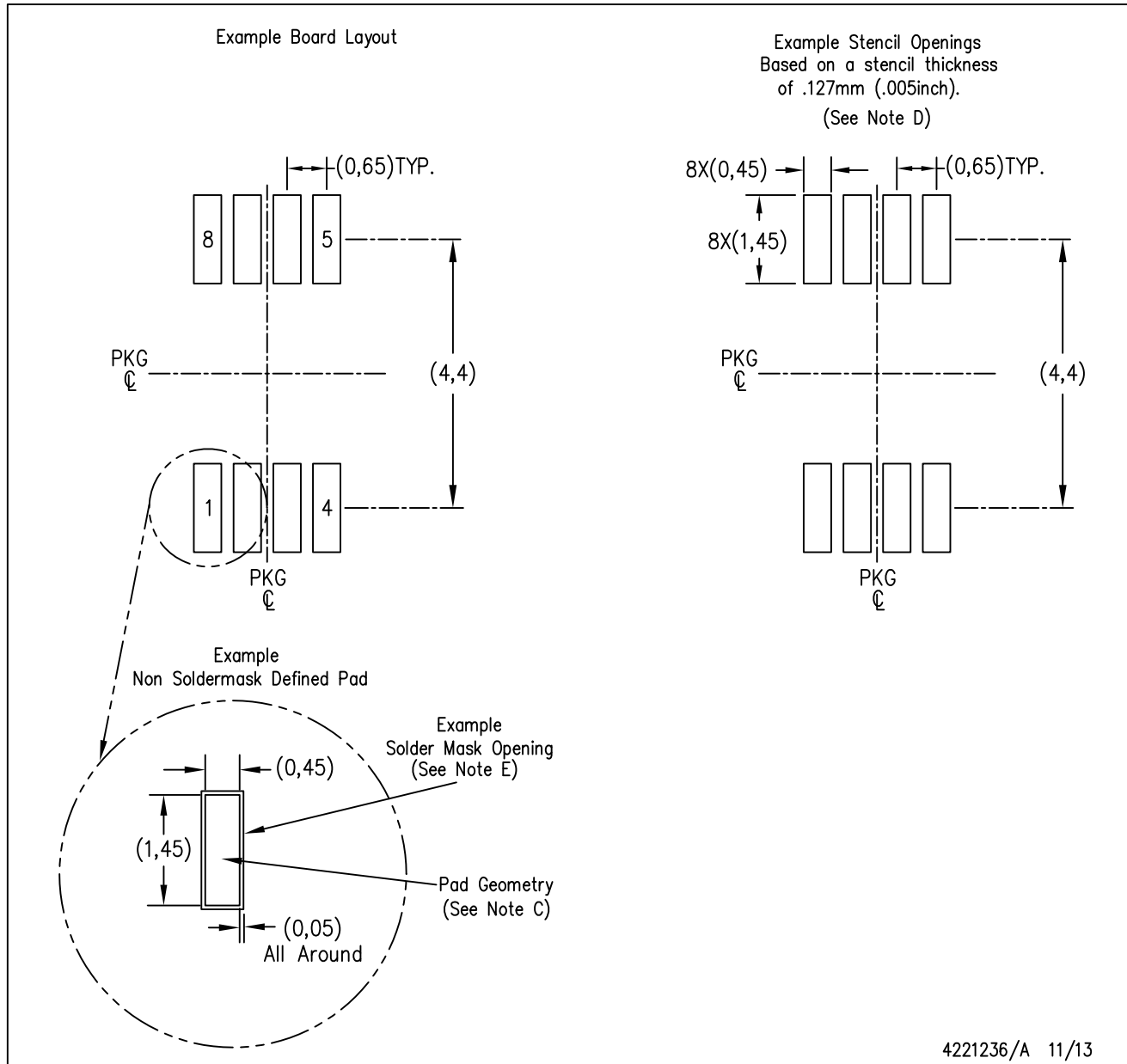


## NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.

DGK (S-PDSO-G8)

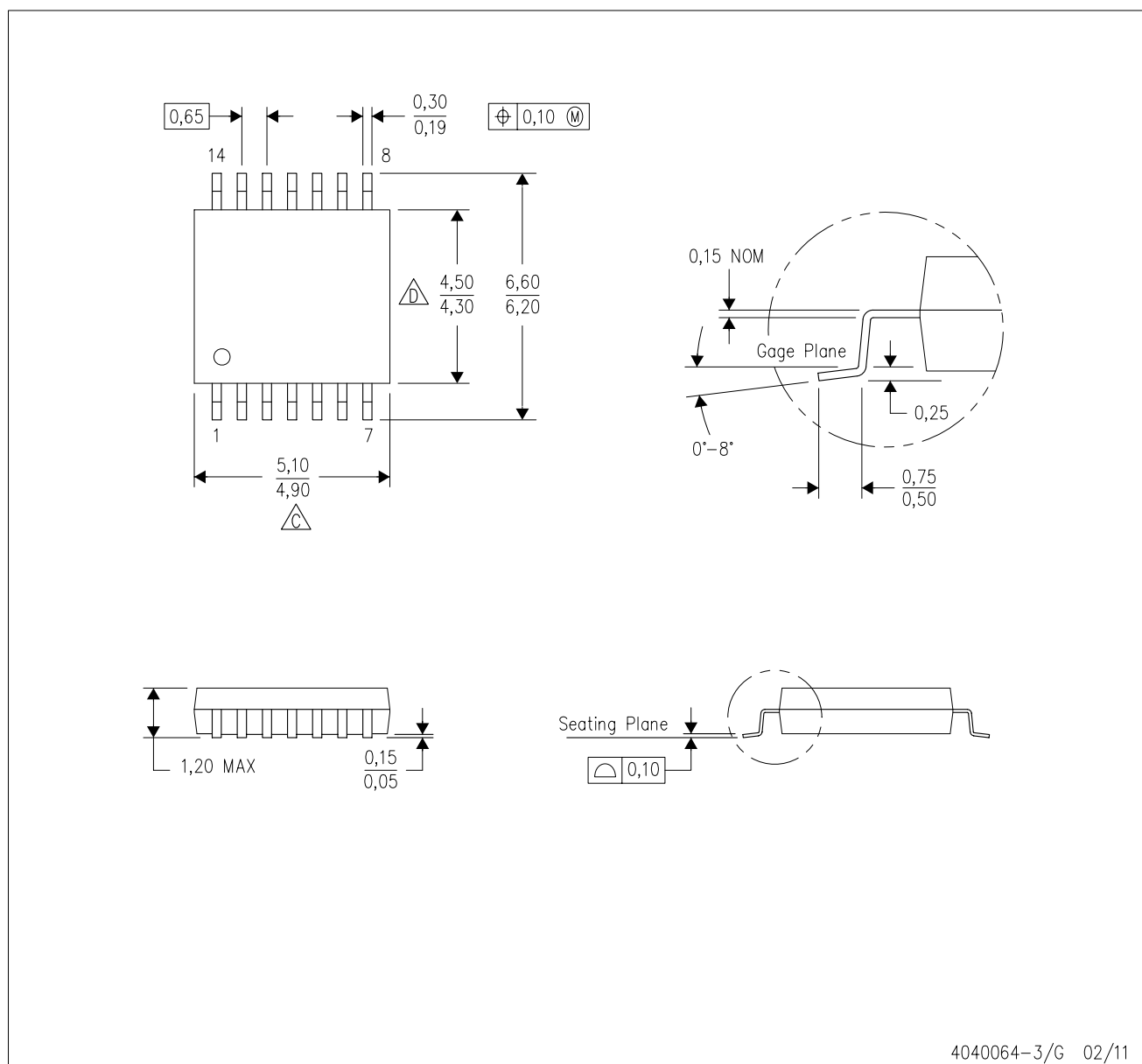
PLASTIC SMALL OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE

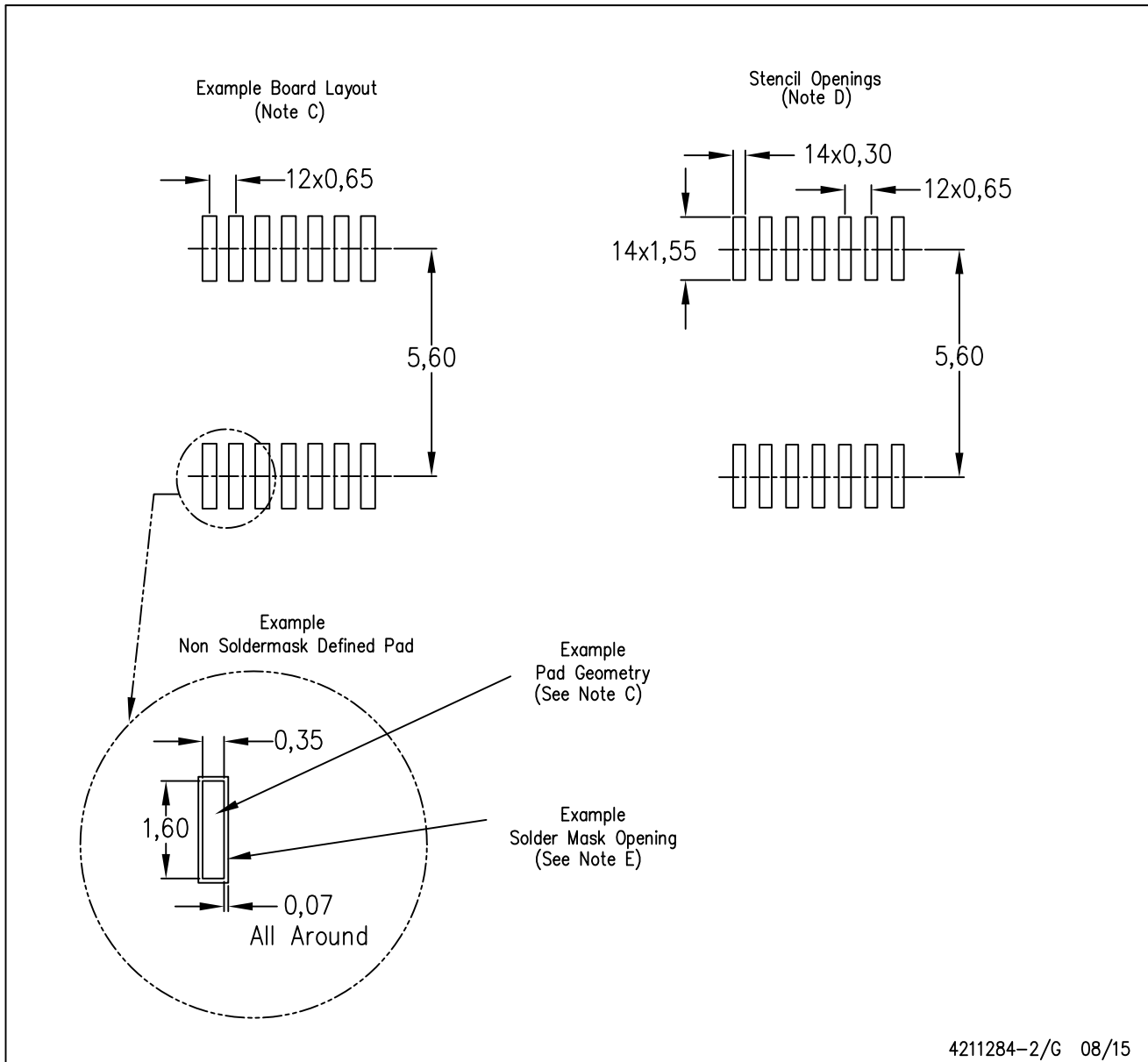


4040064-3/G 02/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
  - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
  - E. Falls within JEDEC MO-153

PW (R-PDSO-G14)

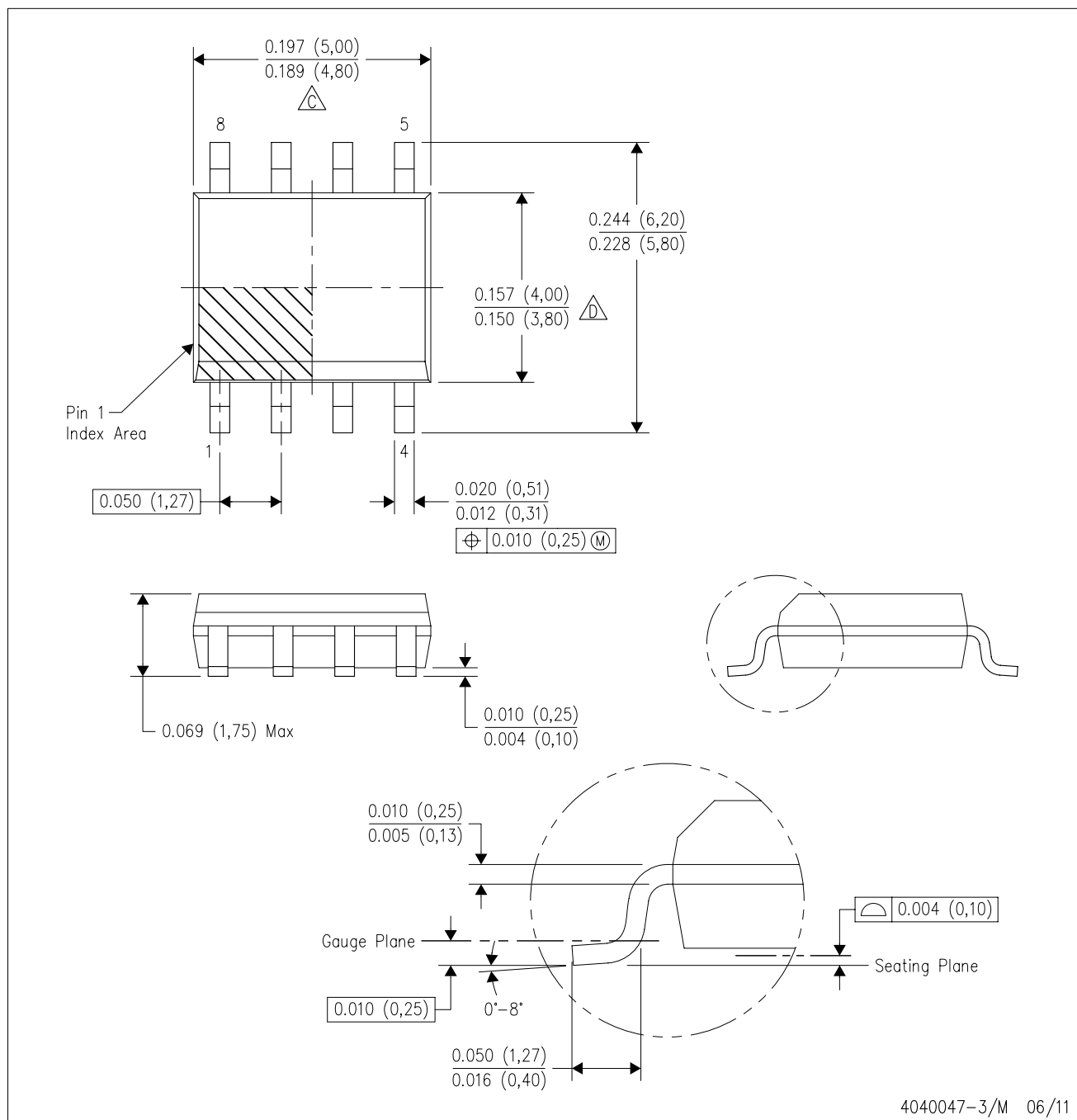
PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE

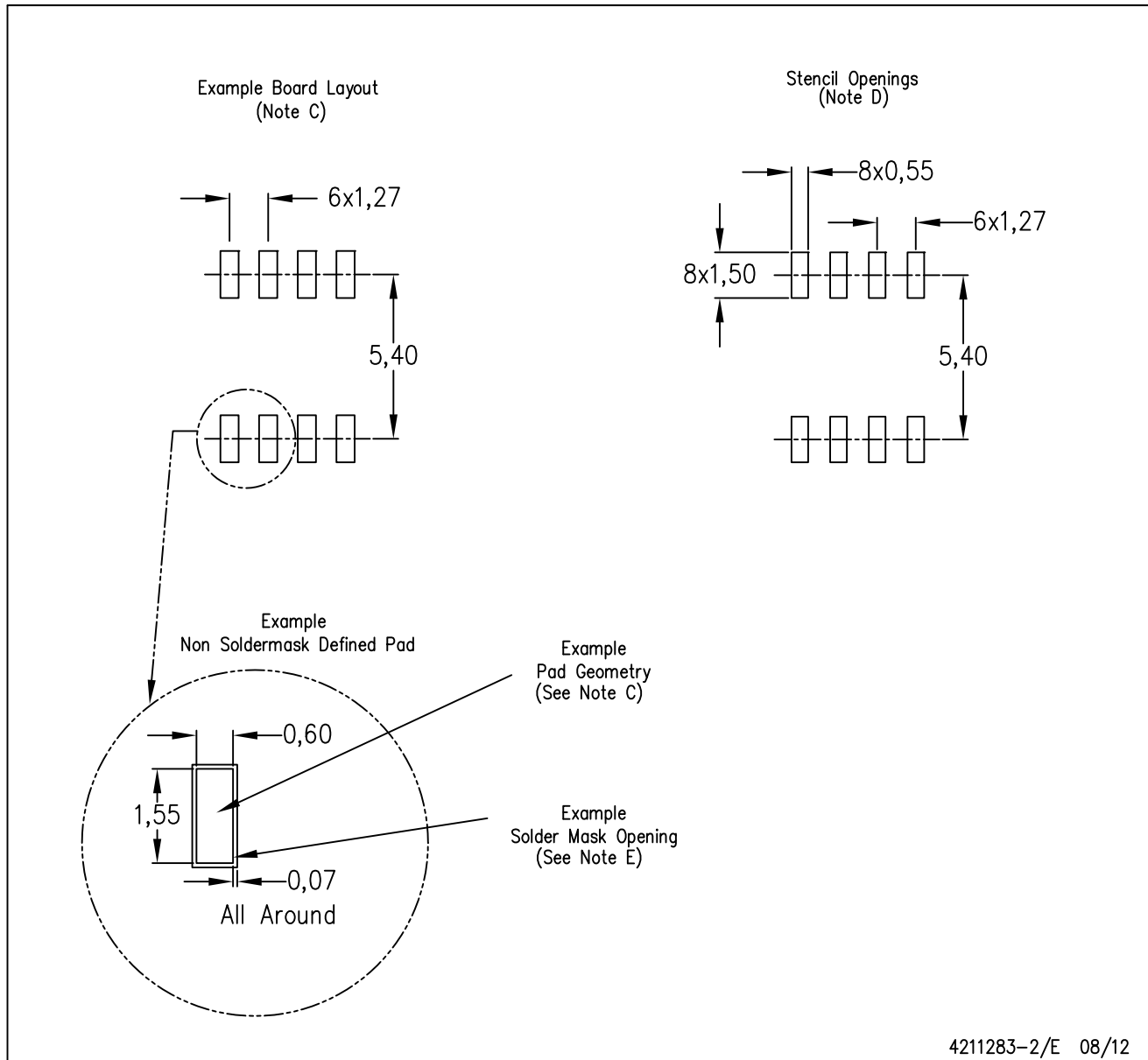


## NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- $\triangle C$  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- $\triangle D$  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

## IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

### Products

Audio	<a href="http://www.ti.com/audio">www.ti.com/audio</a>
Amplifiers	<a href="http://amplifier.ti.com">amplifier.ti.com</a>
Data Converters	<a href="http://dataconverter.ti.com">dataconverter.ti.com</a>
DLP® Products	<a href="http://www.dlp.com">www.dlp.com</a>
DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>
Clocks and Timers	<a href="http://www.ti.com/clocks">www.ti.com/clocks</a>
Interface	<a href="http://interface.ti.com">interface.ti.com</a>
Logic	<a href="http://logic.ti.com">logic.ti.com</a>
Power Mgmt	<a href="http://power.ti.com">power.ti.com</a>
Microcontrollers	<a href="http://microcontroller.ti.com">microcontroller.ti.com</a>
RFID	<a href="http://www.ti-rfid.com">www.ti-rfid.com</a>
OMAP Applications Processors	<a href="http://www.ti.com/omap">www.ti.com/omap</a>
Wireless Connectivity	<a href="http://www.ti.com/wirelessconnectivity">www.ti.com/wirelessconnectivity</a>

### Applications

Automotive and Transportation	<a href="http://www.ti.com/automotive">www.ti.com/automotive</a>
Communications and Telecom	<a href="http://www.ti.com/communications">www.ti.com/communications</a>
Computers and Peripherals	<a href="http://www.ti.com/computers">www.ti.com/computers</a>
Consumer Electronics	<a href="http://www.ti.com/consumer-apps">www.ti.com/consumer-apps</a>
Energy and Lighting	<a href="http://www.ti.com/energy">www.ti.com/energy</a>
Industrial	<a href="http://www.ti.com/industrial">www.ti.com/industrial</a>
Medical	<a href="http://www.ti.com/medical">www.ti.com/medical</a>
Security	<a href="http://www.ti.com/security">www.ti.com/security</a>
Space, Avionics and Defense	<a href="http://www.ti.com/space-avionics-defense">www.ti.com/space-avionics-defense</a>
Video and Imaging	<a href="http://www.ti.com/video">www.ti.com/video</a>

### TI E2E Community

[e2e.ti.com](http://e2e.ti.com)